

TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

MICROWAVE POWER GaAs FET

TIM1112-15L

FEATURES

n **HIGH POWER**

P1dB=42.0dBm at 11.7GHz to 12.7GHz

n **HIGH GAIN**

G1dB=6.0dB at 11.7GHz to 12.7GHz

n **BROAD BAND INTERNALLY MATCHED FET**

n **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Compression Point	P1dB	VDS= 9V f = 11.7 to 12.7GHz	dBm	41.0	42.0	—
Power Gain at 1dB Compression Point	G1dB		dB	5.0	6.0	—
Drain Current	IDS1		A	—	4.5	5.5
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	29	—
3 rd Order Intermodulation Distortion	IM3	Two-tone Test Po=30.0 dBm	dBc	-42	-45	—
Drain Current	IDS2	(Single Carrier Level)	A	—	4.5	5.5
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C	—	—	100

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	mS	—	3000	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	11.5
Gate-Source Breakdown Voltage	VGSO	IGS= -145μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

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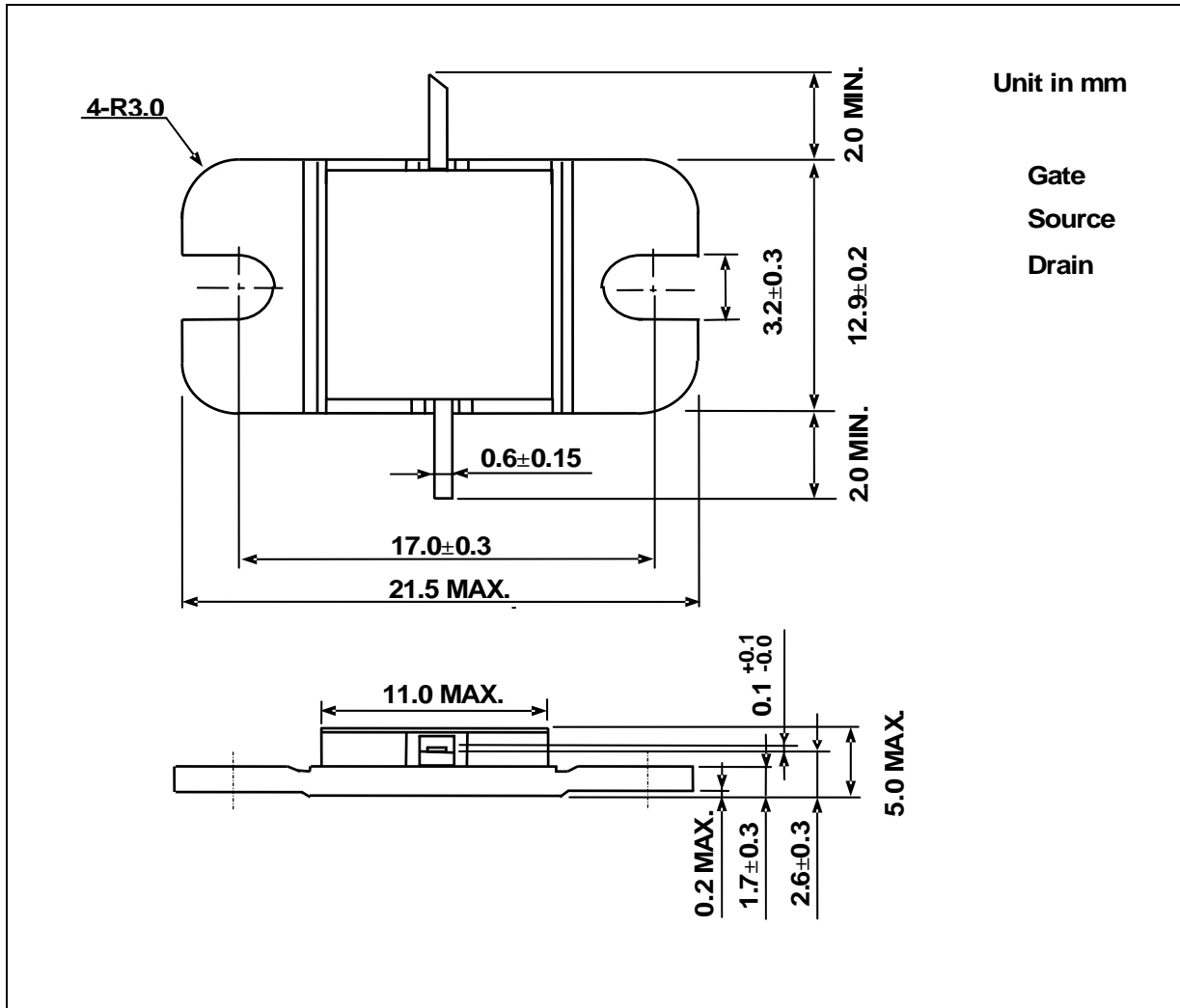
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	11.5
Total Power Dissipation (T _c = 25 °C)	P _T	W	60.0
Channel Temperature	T _{ch}	°C	175
Storage	T _{stg}	°C	-65 ~ +175

PACKAGE OUTLINE (2-11C1B)

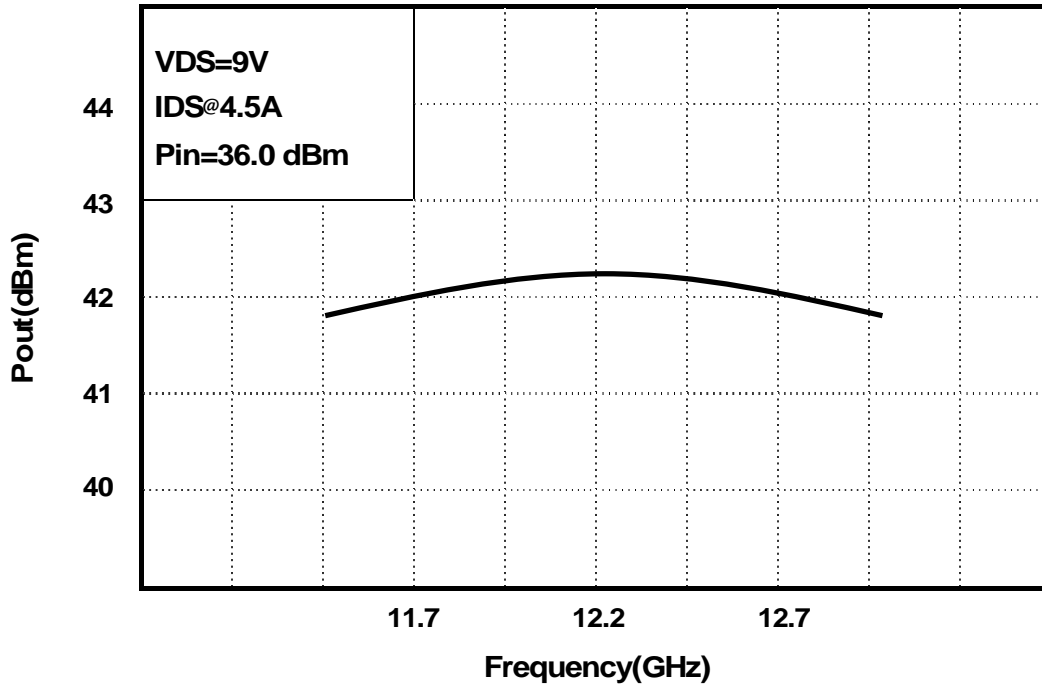


HANDLING PRECAUTIONS FOR PACKAGE MODEL

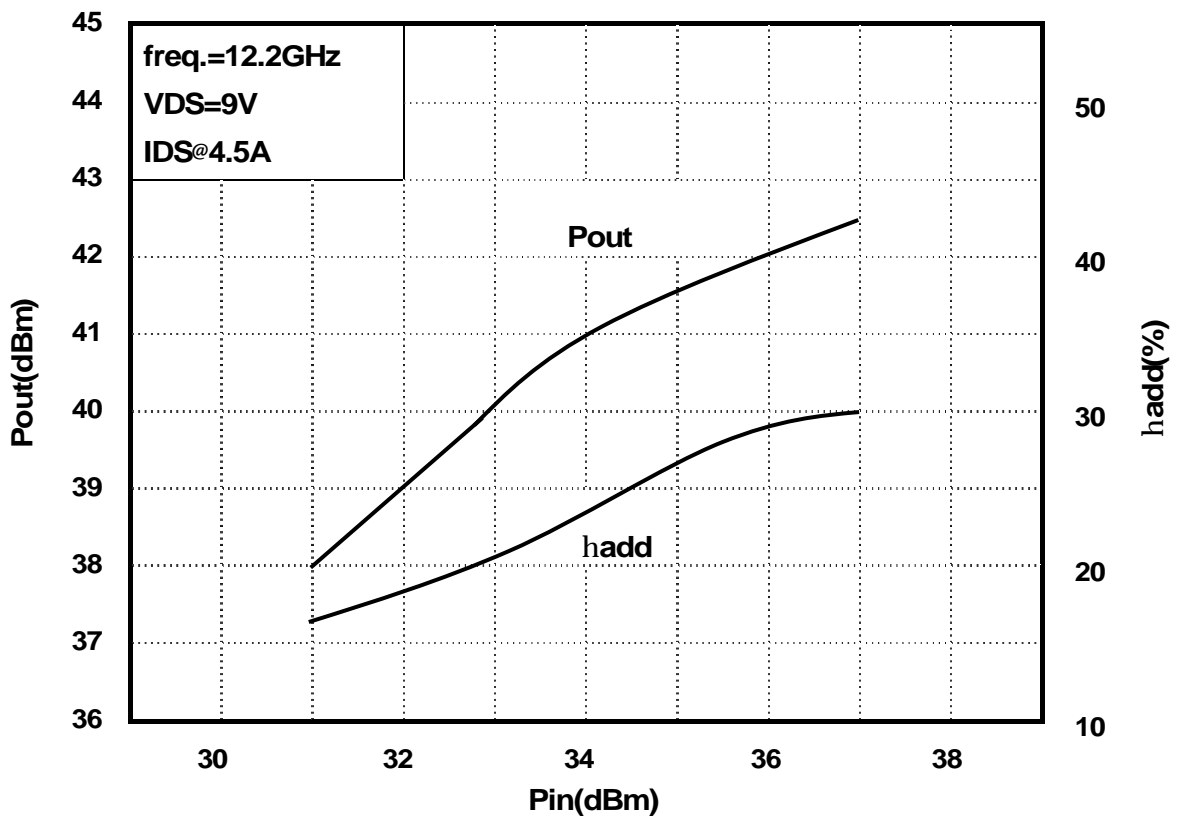
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE

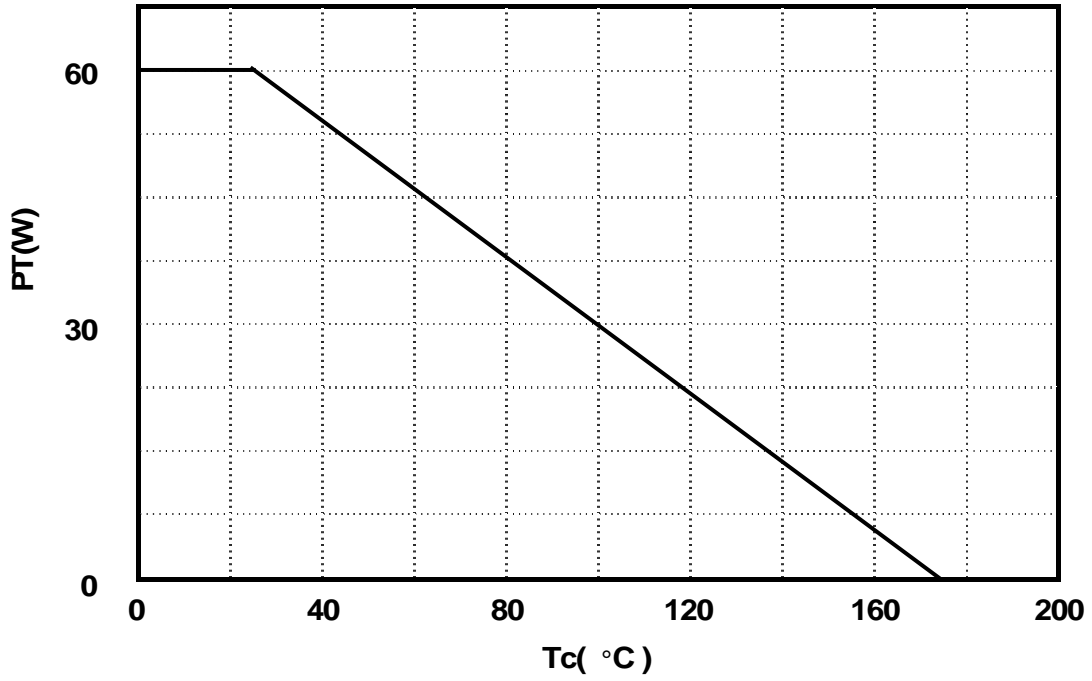
Output Power (Pout) vs. Frequency



Output Power(Pout) vs. Input Power(Pin)



Power Dissipation(PT) vs. Case Temperature(Tc)



IM3 vs. Output Power Characteristics

